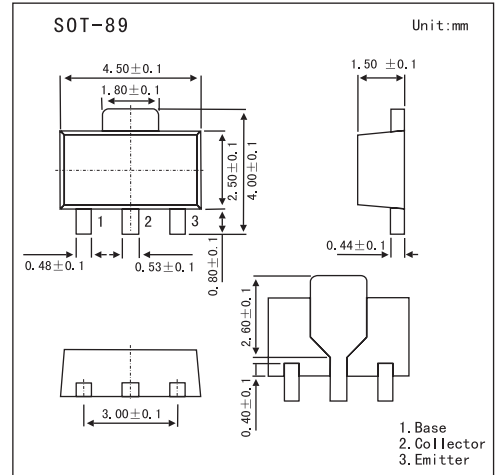


# 2SC4080

■ Features

- High Ft
- High breakdown voltage
- Small reverse transfer capacitance excellent high-frequency characteristic
- Adoption of FBET process



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
collector-base voltage	V <sub>CB0</sub>	200	V
collector-emitter voltage	V <sub>CE0</sub>	200	V
emitter-base voltage	V <sub>EB0</sub>	4	V
collector current	I <sub>C</sub>	100	mA
Collector Current (pulse)	I <sub>CP</sub>	200	mA
Collector Dissipation	P <sub>C</sub>	500	mA
		1.3	W
Junction Temperature	T <sub>J</sub>	150	°C
storage Temperature	T <sub>stg</sub>	-55 to 150	°C

\*Mounted on ceramic board (250mm<sup>2</sup>X0.8mm)

## 2SC4080

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
collector cutoff Current	ICBO	V <sub>CB</sub> =150V, I <sub>E</sub> =0			0.1	μA
Emitter cutoff current	IEBO	V <sub>EB</sub> =2V, I <sub>C</sub> =0			1.0	μA
DC Current Gain	hFE	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA	40		320	
		V <sub>CE</sub> =10V, I <sub>C</sub> =100mA	20			
Gain-Bandwidth product	fr	V <sub>CE</sub> =30V, I <sub>C</sub> =30mA		400		MHz
Output Capacitance	cob	V <sub>CB</sub> =30V, f=1MHz		1.8		pF
Reverse Transfer	cre	V <sub>CB</sub> =30V, f=1MHz		1.4		
Collector to Emitter Saturation Voltage	V <sub>CE(sat)</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			1	V
Base to Emitter Stauration Voltage	V <sub>BE(sat)</sub>	I <sub>C</sub> =20mA, I <sub>B</sub> =2mA			1	V
Collector to Base Breakdown Voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =10μA, I <sub>E</sub> =0	200			V
Collector to Emitter Breakdown Voltage	V <sub>(BR)CEO</sub>	I <sub>C</sub> =1mA, I <sub>B</sub> =0	200			V
Emitter to Base Breakdown Voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =100μA, I <sub>C</sub> =0	4			V

■ hFE Classification

Marking	CI			
	C	D	E	F
Type	40 to 80	60 to 120	100 to 200	160 to 320